

Current

9 A

600V N-Channel Super Junction MOSFET

Voltage

Features

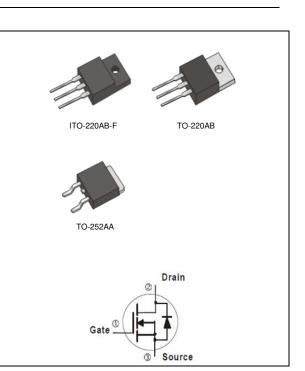
R_{DS(ON)}, V_{GS}@10V, I_D@2.8A<0.535Ω

600 V

- Fast switching speed
- Low on-resistance
- Low Noise
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : TO-252AA, TO-220AB, ITO-220AB-F
- Terminals : Solderable per MIL-STD-750, Method 2026
- TO-252AA Approx. Weight : 0.0104 ounces, 0.297grams
- TO-220AB Approx. Weight : 0.067 ounces, 1.89 grams
- ITO-220AB-F Approx. Weight : 0.068 ounces, 2 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	TO-220AB	ITO-220AB-F	TO-252AA	UNITS	
Drain-Source Voltage		V _{DS}	600			V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20				
Continuous Drain Current (Note 4)	T _C =25°C		9				
	$T_{C}=100^{\circ}C$	I _D	5			А	
Pulsed Drain Current (Note 1)		I _{DM}	18]	
Power Dissipation (Note 3)	T _C =25°C	P _D	94	48	94	w	
	T _C =100°C		38	19	38		
Continuous Drain Current (Note 4)	T _A =25°C		1.3			Α	
	T _A =70°C	l _D					
Power Dissipation	T _A =25°C	P _D	2	1.04	2	W	
	T _A =70°C		1.3	0.9	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	98			mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150			°C	
							ypical Thermal Resistance (Note 4,5)
 Limited only By Maximum Junction 		$R_{ extsf{ heta}JA}$	62.5	120	62.5	°C/W	

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Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

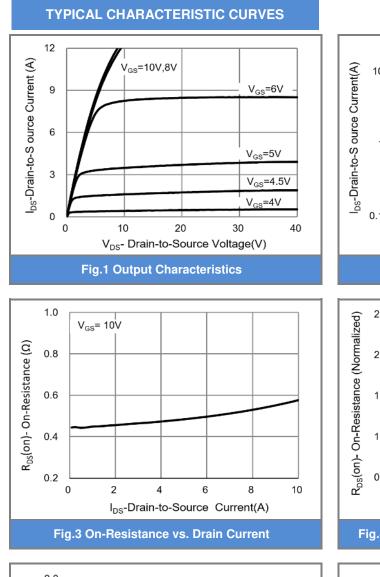
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static		·	·			
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I _D =250uA	600	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	2	2.98	4	
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =10V, I_{D} =2.8A	-	0.45	0.535	Ω
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =600V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Diode Forward Voltage	V _{SD}	$I_S=9A, V_{GS}=0V$	-	0.98	1.5	V
Transconductance	GFS	Vds=10V, Id=4.5A	-	4.5	-	S
Dynamic (Note 7)						
Total Gate Charge	Qg	V _{DS} =300V, I _D =9A, V _{GS} =10V ^(Note 2,3)	-	23.7	-	nC
Gate-Source Charge	Q _{gs}		-	3.5	-	
Gate-Drain Charge	Q_gd	V _{GS} =10V	-	13.3	-	
Gate Input Resistance	R _g	F = 1MHz	-	10.1	-	Ω
Input Capacitance	Ciss		-	531	-	pF
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$	-	547	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	69	-	
Turn-On Delay Time	td _(on)		-	11	-	
Turn-On Rise Time	tr	$V_{DD}=300V, I_{D}=4.5A,$ $R_{G}=10\Omega^{(Note 2,3)}$	-	26	-	
Turn-Off Delay Time	td _(off)	$R_{G}=10\Omega$	-	69	-	
Turn-Off Fall Time	t _f		-	26	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S		-	-	9	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}		-	-	18	
Reverse Recovery Time	trr	V _{GS} =0V, I _S =9A	-	354	-	ns
Reverse Recovery Charge	Qrr	dI _F / dt=100A/us ^(Note 2)	-	4.3	-	uC

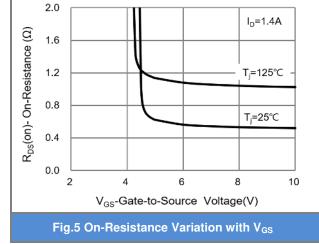
NOTES :

1. Pulse width <300us, Duty cycle <2%.

- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. TO-252AA mounted on a 1 inch2 with 2oz.square pad of copper.
- 6. L=100mH, I_{AS} =1.4A, V_{DD} =50V, R_{G} =25 ohm, Starting T_{J} =25°C.
- 7. Guaranteed by design, not subject to production testing.







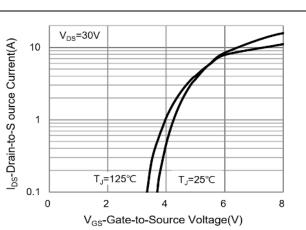


Fig.2 Transfer Characteristics

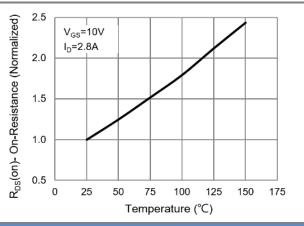
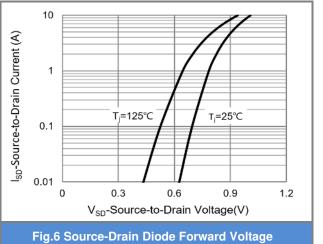


Fig.4 On-Resistance vs. Junction Temperature





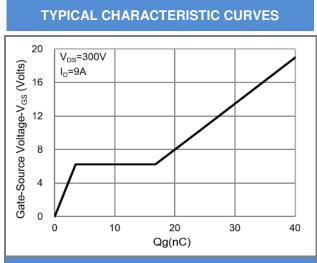


Fig.7 Gate-Charge Characteristics

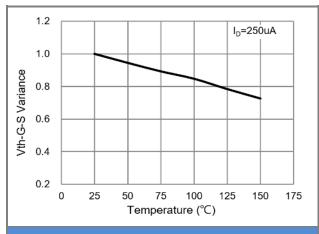
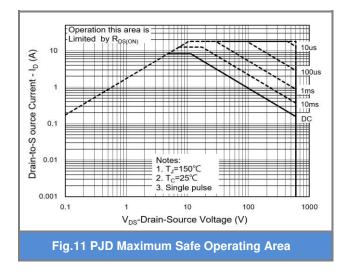
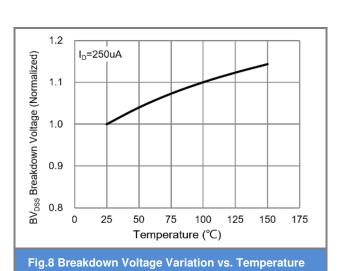
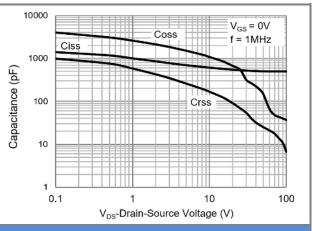


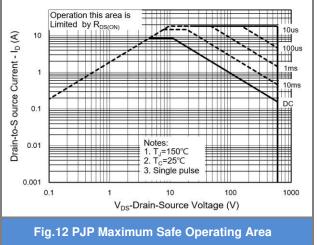
Fig.9 Threshold Voltage Variation with Temperature



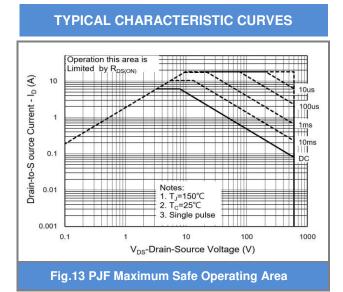












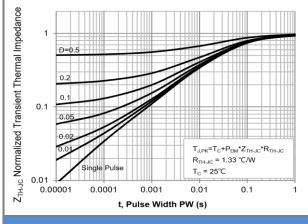
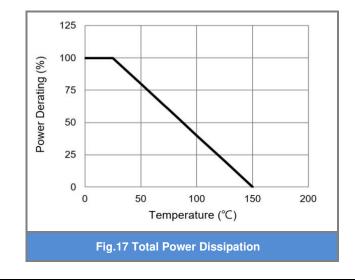


Fig.15 PJP Normalized Transient Thermal Impedance



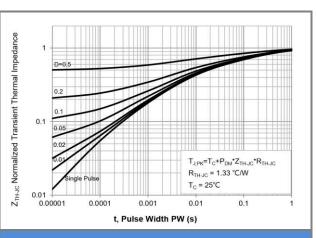


Fig.14 PJD Normalized Transient Thermal Impedance

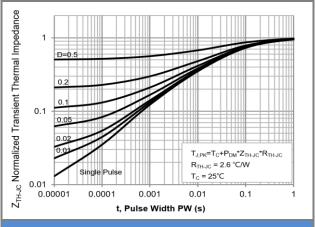
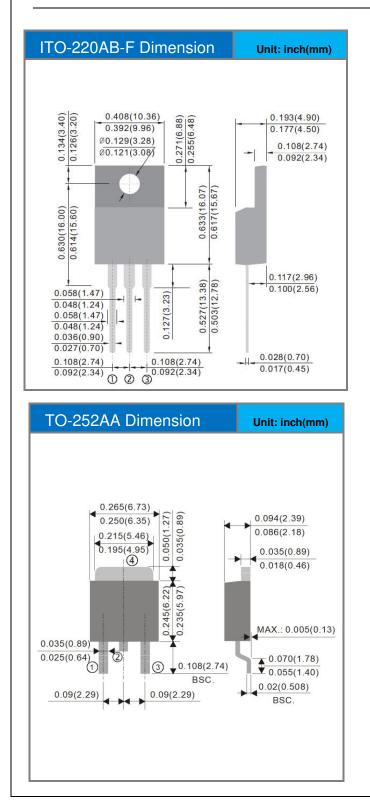
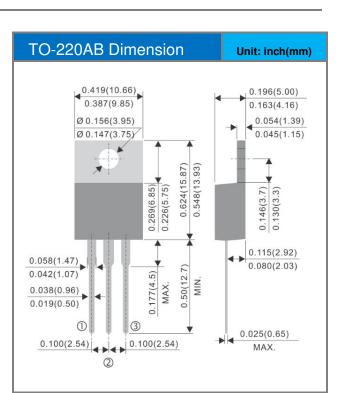


Fig.16 PJF Normalized Transient Thermal Impedance



Packaging Information









Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD60R540E_L2_00001	TO-252AA	3,000pcs / 13" reel	60R540E	Halogen free
PJP60R540E_T0_00001	TO-220AB	50pcs / Tube	60R540E	Halogen free
PJF60R540E_T0_00001	ITO-220AB-F	50pcs / Tube	60R540E	Halogen free





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